



Semiconductors: XRay Writing of Metallic Conductivity and Oxygen Vacancies at Silicon/SrTiO₃ Interfaces (Adv. Funct. Mater. 25/2019)

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SEMICONDUCTORS

Two-dimensional electronic states at interfaces are often endowed with novel properties that are promising for future technological applications. Defects at oxide interfaces, in particular, oxygen vacancies play a major role in controlling electronic and magnetic properties at the interfaces. In article number 1900645, Alla Chikina and co-workers report lithography-like writing of a metallic state at the interface between SrTiO_3 and amorphous Si using X-ray irradiation.

